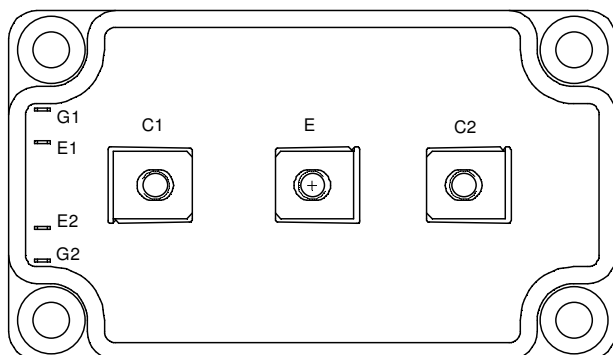
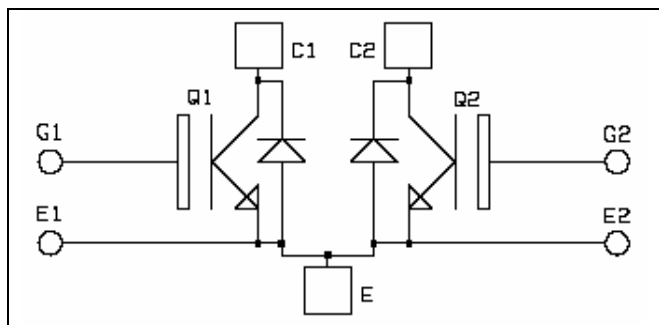


Dual common source NPT IGBT Power Module

**$V_{CES} = 1200V$
 $I_C = 300A @ T_c = 80^\circ C$**



Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$ 400	A
		$T_c = 80^\circ C$ 300	
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$ 800	
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$ 2080	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$ 600A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 4mA$	1200			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 1200V$		0.4	6	mA
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		25		
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_C = 300A$		3.3	3.9	V
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		4		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 12mA$	4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$			± 1	μA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		21		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		2.9		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		1.52		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 300A$ $R_G = 2\Omega$		70		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			500		
T_f	Fall Time			30		
E_{on}	Turn-on Switching Energy			17		mJ
E_{off}	Turn-off Switching Energy			18		

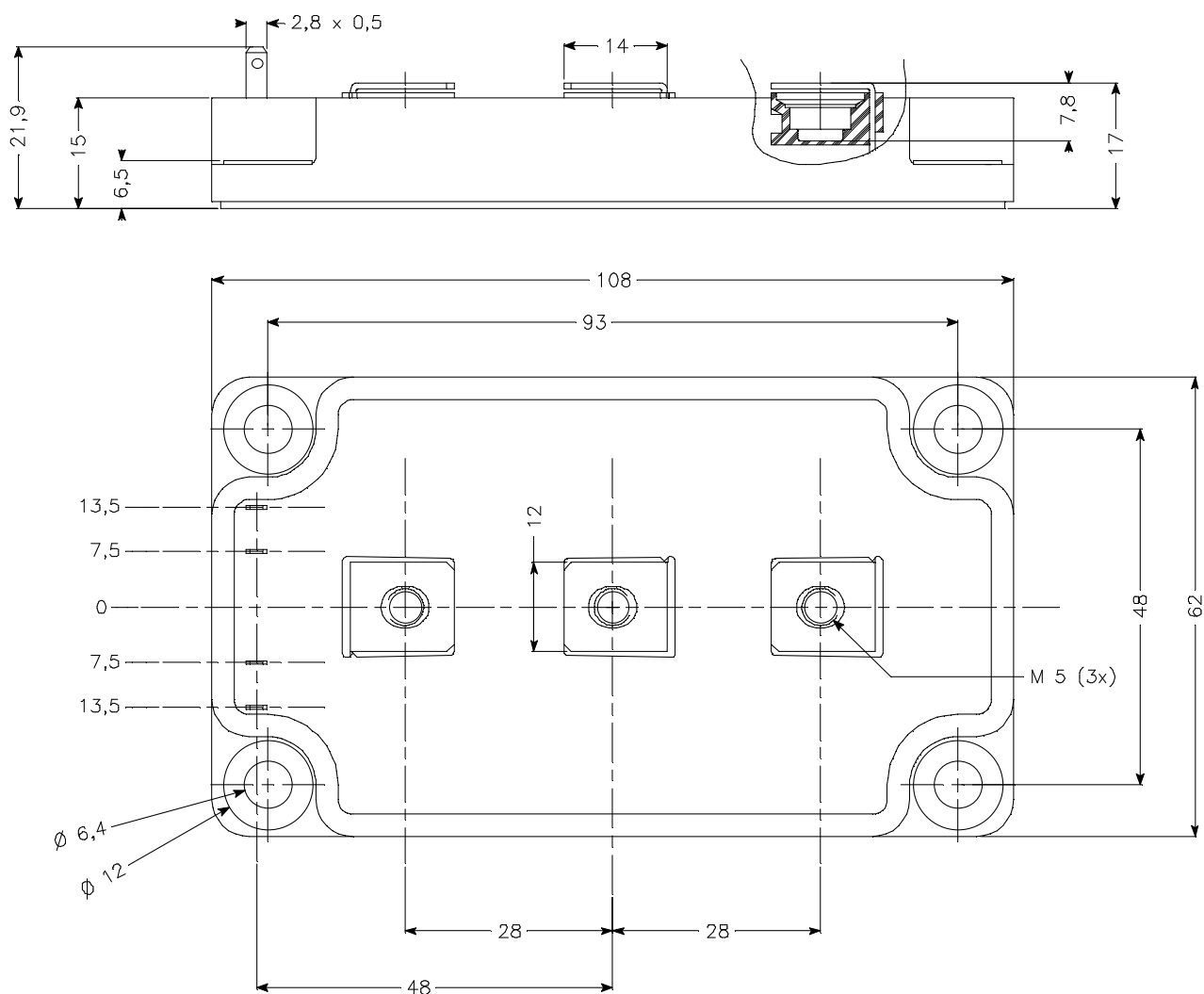
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle $T_c = 85^\circ\text{C}$		250		A
V_F	Diode Forward Voltage	$I_F = 300A$		2.2	2.5	V
		$I_F = 400A$		2.4		
		$I_F = 400A$ $T_j = 150^\circ\text{C}$		2.2		
Q_{rr}	Reverse Recovery Charge	$I_F = 300A$ $T_j = 25^\circ\text{C}$		13		μC
		$T_j = 125^\circ\text{C}$		40		

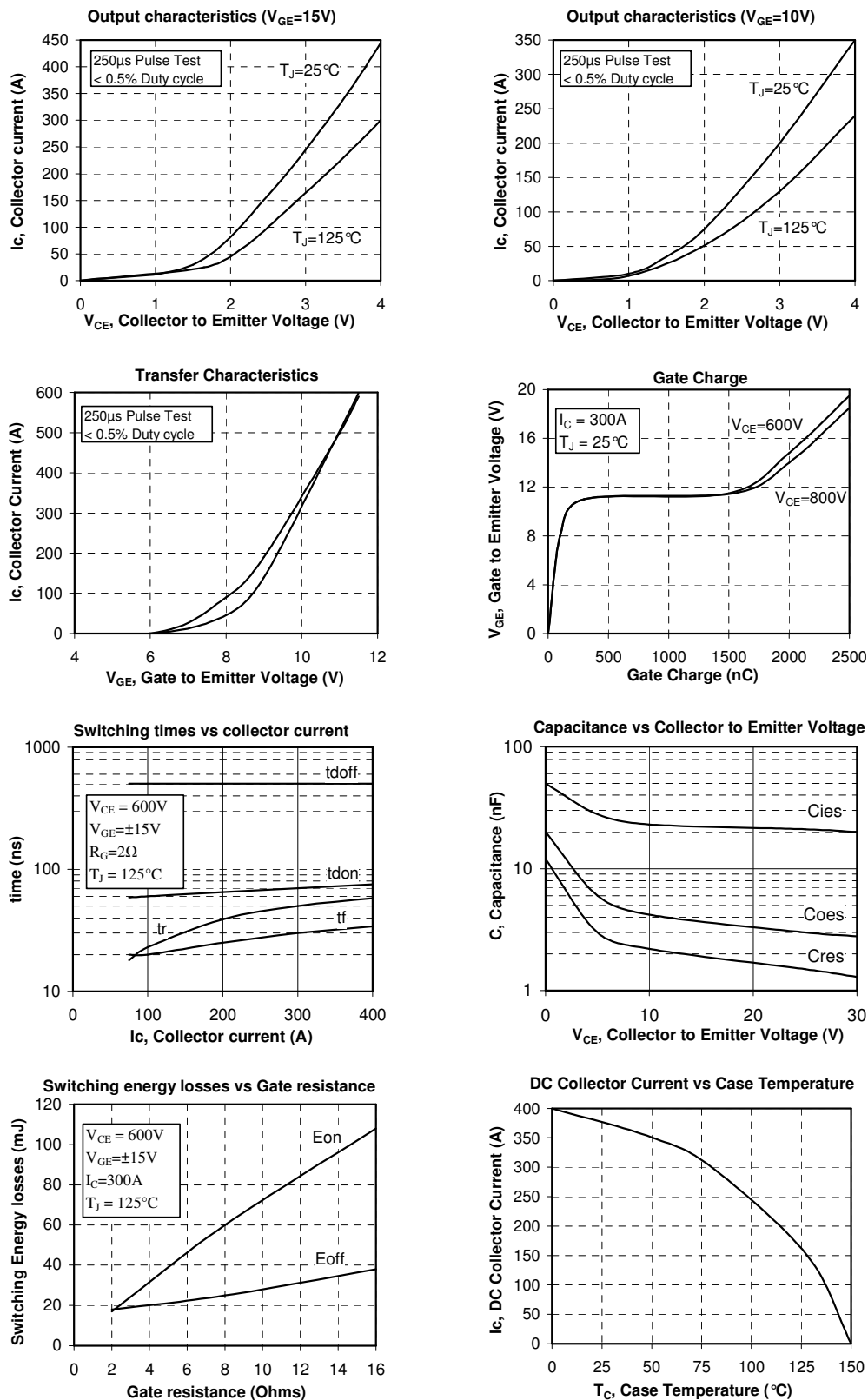
Thermal and package characteristics

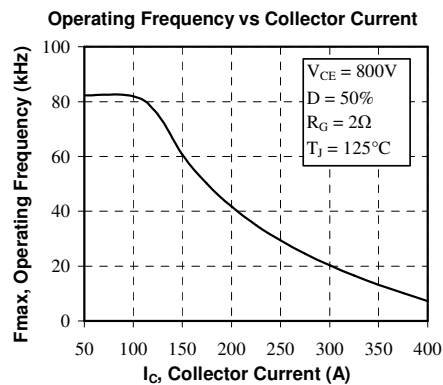
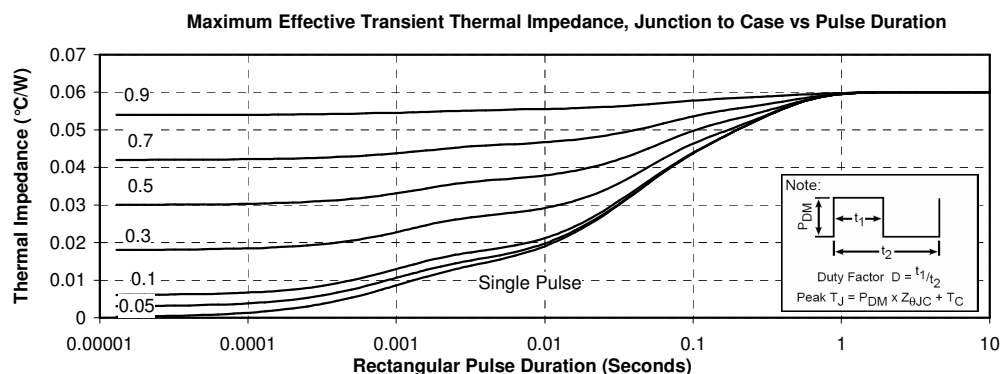
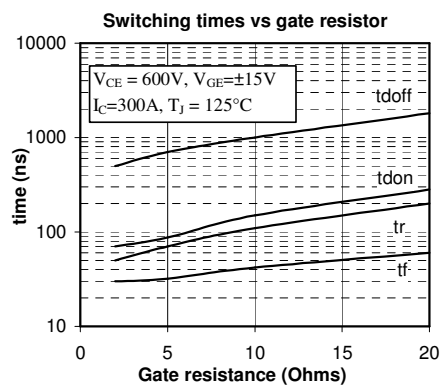
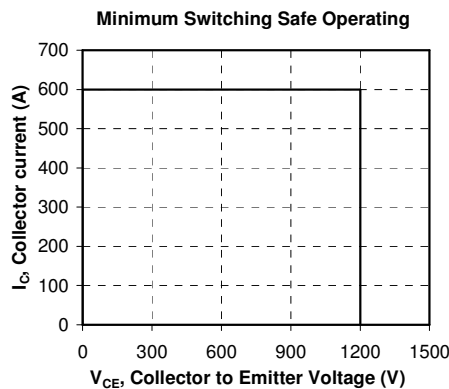
Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case	IGBT			0.06	°C/W
		Diode			0.13	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

Package outline



Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.